NEC

NPN SILICON TRANSISTOR

2SD774

DESCRIPTION

The 2SD774 is designed for use in driver and output stages of audio frequency amplifiers.

FEATURES

High Total Power Dissipation P_T: 1.0 W (Ta = 25 °C)

High Voltage

VCE: 50 V MIN.

Complementary to the NEC 2SB734 FNP Transistor.

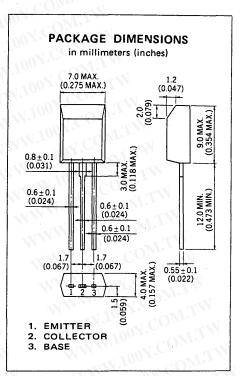
ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Maximum Power Dissipation (Ta=25 °C)

Total Power Dissipation 1.0 W

Maximum Voltages and Current (Ta=25 °C)



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ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1	DC Current Gain	135	300	600	$CO_{\overline{M}}$	V _{CE} =2.0 V, I _C =100 mA
hFE2	DC Current Gain	70			CON.	V _{CE} =1.0 V, I _C =1.0 A
fT	Gain Bandwidth Product	50	95		MHz	V _{CE} =2.0 V, I _E =-10 mA
C _{ob}	Output Capacitance		16	35	pF	V _{CB} =10 V, I _E =0, f=1.0 MHz
I _{СВО}	Collector Cutoff Current			100	nA	V _{CB} =50 V, I _E =0
I _{EBO}	Emitter Cutoff Current			100	nA	V _{EB} =6.0 V, I _C =0
VBE	Base to Emitter Voltage	0.55	0.60	0.65	vCO.	V _{CE} =6.0 V, I _C =5.0 mA
VCE(sat)	Collector Saturation Voltage		0.23	0.30	100 0	I _C =1.0 A, I _B =50 mA
V _{BE(sat)}	Base Saturation Voltage		0.92	1.20	100	IC=1.0 A, IB=50 mA

Classification of hFE1

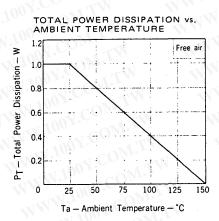
Rank	L ₂	К3	κ ₄	U ₄	U ₅ .
Range	135 — 270	200 – 320	250 – 400	300 – 480	360 – 600

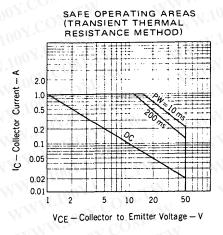
Test Conditions: VCE=2.0 V, IC=100 mA.

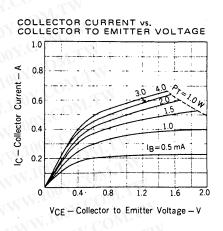


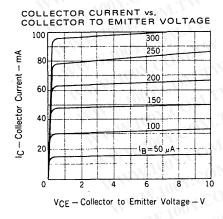
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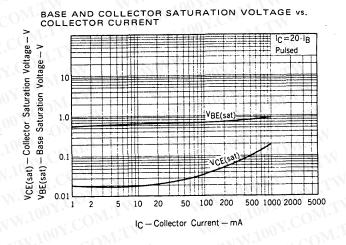
TYPICAL CHARACTERISTICS (Ta=25 °C)

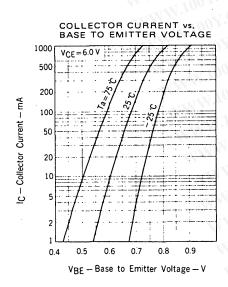


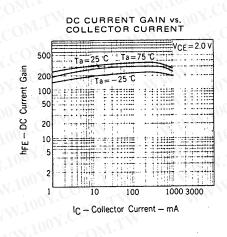


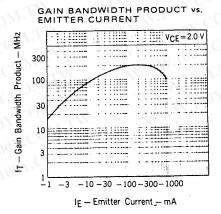






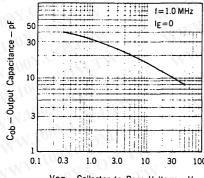








OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



VCB - Collector to Base Voltage - V

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